

1765  
PATENT

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: E. Morita

Serial No.: 09/726,860

Filed: November 30, 2000

For: METHOD OF MANUFACTURING  
CRYSTAL OF III-V COMPOUND OF THE  
NITRIDE SYSTEM, CRYSTAL  
SUBSTRATE OF III-V COMPOUND OF  
THE NITRIDE SYSTEM, CRYSTAL FILM  
OF III-V COMPOUND OF THE NITRIDE  
SYSTEM, AND METHOD OF  
MANUFACTURING DEVICE

Case No.: 9792909-4715

Examiner: M. Anderson

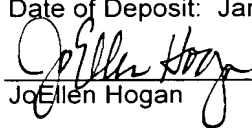
Group Art Unit: 1765

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JoEllen Hogan1/2/02  
Date**TRANSMITTAL LETTER**

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

Enclosed herewith is a Response to Restriction Requirement and  
Supplemental Preliminary Amendment of E. Morita in the above-identified patent  
application.

Also enclosed are: Return Receipt Postcard

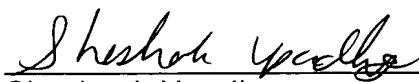
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Respectfully submitted,

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#17/B  
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2/5/02

Inventor: E. Morita

Examiner: M. Anderson

Serial No.: 09/726,860

Group Unit: 1765

Title: Method of Manufacturing Crystal...

Atty. Docket No. 9792909-4715

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Response to Restriction Requirement and Supplemental Preliminary Amendment

In response to the Office Action dated, 03 Dec. 2001, requiring restriction of the claims, the applicant responds as follows.

A. In the Claims

Applicant provisionally elects Group I - corresponding to claims 1 to 16, drawn to the method.

Please cancel, without prejudice, claims 17-30 drawn to the substrate product.

Please also amend claims 1 to 16 as follows.

1. (Amended) A method of manufacturing a crystal of a III-V compound of the nitride system, the method including:

a first growth step [of forming] to form a first crystal layer, the first crystal layer further having a surface, by growing a crystal of a III-V compound of the nitride system on [the] a surface of a basal body;

a first mask forming step [of forming] to form a first mask pattern on the surface of the first crystal layer;